

# PSMNR82-30YLE

N-channel 30 V, 0.87 mOhm, ASFET for hotswap with enhanced SOA in LFPAK56

**10 November 2022** 

Product data sheet

### 1. General description

N-channel enhancement mode ASFET for hotswap with enhanced SOA in LFPAK56 package optimized for low  $R_{DSon}$  and strong safe operating area, optimized for hot-swap, inrush and linear-mode applications.

#### 2. Features and benefits

- Fully optimized Safe Operating Area (SOA) for superior linear mode operation
- Optimized for low R<sub>DSon</sub> / low I<sup>2</sup>R conduction losses
- LFPAK56E package for applications that demand the highest performance and reliability in a 30 mm<sup>2</sup> footprint
- Low leakage < 1 μA at 25 °C</li>
- · Copper-clip for low parasitic inductance and resistance
- High reliability LFPAK package, qualified to 175 °C

### 3. Applications

- Hot swap in 12 V-20 V applications
- · e-Fuse
- · DC switch
- · Load switch
- Battery protection

#### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	30	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	330	Α	
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	268	W	
Tj	junction temperature			-55	-	175	°C	
Static characte	Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 10		-	0.73	0.87	mΩ	
		$V_{GS} = 7 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C}; Fig. 10$		-	0.87	1.25	mΩ	
Dynamic chara	Dynamic characteristics							
$Q_{GD}$	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$		1.8	10	20	nC	
Q <sub>G(tot)</sub>	total gate charge	T <sub>j</sub> = 25 °C; <u>Fig. 12; Fig. 13</u>		18	41	68	nC	



Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Source-drain diode							
S	softness factor	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$ $V_{DS} = 15 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$		-	1.03	-	

<sup>[1] 330</sup> A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

### 5. Pinning information

#### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	mb	
2	S	source		D
3	S	source	a	
4	G	gate		G_(□□□□)
mb	D	mounting base; connected to drain		mbb076 S

## 6. Ordering information

#### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PSMNR82-30YLE	LFPAK56; Power-SO8	plastic, single-ended surface-mounted package; 4 terminals	SOT669		

## 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PSMNR82-30YLE	E82L30Y

## 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Tj = 25  $^{\circ}$ C unless otherwise stated.

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	30	V
$V_{DGR}$	drain-gate voltage	25 °C ≤ $T_j$ ≤ 175 °C; $R_{GS}$ = 20 kΩ		-	30	V
$V_{GS}$	gate-source voltage			-20	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	268	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	330	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>		-	295	Α
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$ ; Fig. 3		-	1667	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C

PSMNR82-30YLE

Symbol	Parameter	Conditions		Min	Max	Unit
$T_{sld(M)}$	peak soldering temperature			-	260	°C
Source-drain	diode		'		'	
Is	source current	T <sub>mb</sub> = 25 °C		-	268	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \mu s$ ; $T_{mb} = 25 °C$		-	1667	Α
Avalanche ru	ggedness					
E <sub>DS(AL)S</sub>		$I_D$ = 25 A; $V_{sup}$ ≤ 30 V; $R_{GS}$ = 50 Ω; $V_{GS}$ = 10 V; $T_{j(init)}$ = 25 °C; unclamped; $t_p$ = 5.5 ms	[2]	-	2.7	J
I <sub>AS</sub>	non-repetitive avalanche current	$V_{sup} \le 30 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ $R_{GS} = 50 \Omega$	[2]	-	190	А

<sup>[1] 330</sup> A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

<sup>[2]</sup> Protected by 100% test.

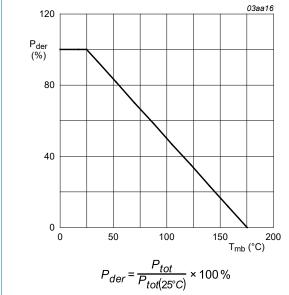
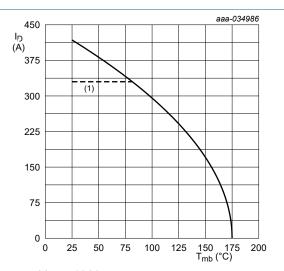


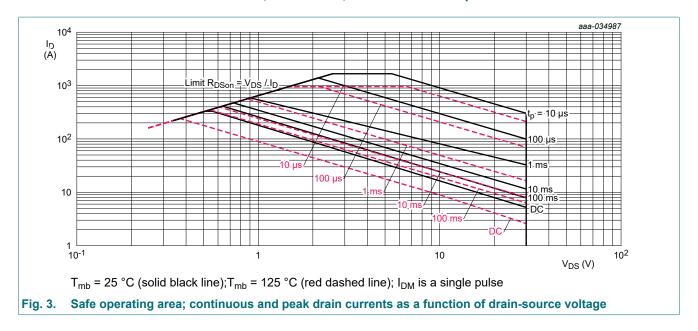
Fig. 1. Normalized total power dissipation as a function of mounting base temperature



 $V_{GS} \ge 10 \text{ V}$  (1) 330 A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

Fig. 2. Continuous drain current as a function of mounting base temperature

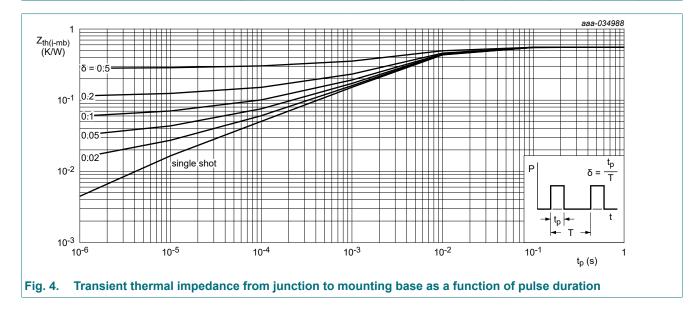
**Product data sheet** 



#### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 4	-	0.42	0.56	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	Fig. 5 Fig. 6	-	42 85	-	K/W K/W



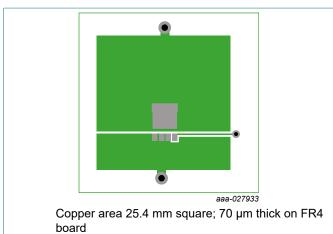
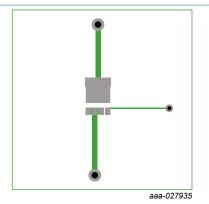


Fig. 5. PCB layout for thermal resistance from junction to ambient



70 µm thick copper on FR4 board

Fig. 6. PCB layout with minimum footprint for thermal resistance from junction to ambient

### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static charac	cteristics					
V <sub>(BR)DSS</sub>	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	30	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 2 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.2	1.79	2.2	V
$\Delta V_{GS(th)}/\Delta T$	gate-source threshold voltage variation with temperature	25 °C ≤ T <sub>j</sub> ≤ 150 °C	-	-3.7	-	mV/K
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 24 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μA
		V <sub>DS</sub> = 24 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	7.2	-	μΑ
I <sub>GSS</sub>	gate leakage current	$V_{GS} = 16 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	-	100	nA
		V <sub>GS</sub> = -16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 25 A; $T_j$ = 25 °C; Fig. 10	-	0.73	0.87	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; Fig. 11	-	-	1.6	mΩ
		V <sub>GS</sub> = 7 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	0.87	1.25	mΩ
		V <sub>GS</sub> = 7 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 150 °C; Fig. 11	-	-	2.3	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	1.3	3.2	8	Ω
Dynamic cha	racteristics		<u>'</u>			<u> </u>
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V; T <sub>j</sub> = 25 °C; <u>Fig. 12</u> ; <u>Fig. 13</u>	18	41	68	nC
		I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C; <u>Fig. 12</u> ; <u>Fig. 13</u>	41	90	149	nC
		I <sub>D</sub> = 0 A; V <sub>DS</sub> = 0 V; V <sub>GS</sub> = 10 V; T <sub>j</sub> = 25 °C	-	46	-	nC

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Q <sub>GS</sub>	gate-source charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 4.5 V;		5	19	36	nC
Q <sub>GS(th)</sub>	pre-threshold gate- source charge	T <sub>j</sub> = 25 °C; <u>Fig. 12</u> ; <u>Fig. 13</u>		2.7	10	19	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate- source charge			2.4	9	17	nC
Q <sub>GD</sub>	gate-drain charge			1.8	10	20	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 15 V; T <sub>j</sub> = 25 °C; Fig. 12; Fig. 13		-	3.2	-	V
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 15 V; V <sub>GS</sub> = 0 V; f = 1 MHz;		4052	6754	10131	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 14</u>		1234	2056	3084	pF
C <sub>rss</sub>	reverse transfer capacitance			93	343	823	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 15 \text{ V}; R_L = 0.6 \Omega; V_{GS} = 4.5 \text{ V};$		-	49	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}C$		-	95	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	37	-	ns
t <sub>f</sub>	fall time			-	44	-	ns
Q <sub>oss</sub>	output charge	$V_{GS} = 0 \text{ V}; V_{DS} = 15 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}$		-	49	-	nC
Source-drai	n diode				_		
V <sub>SD</sub>	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 15$		-	0.78	1	V
t <sub>rr</sub>	reverse recovery time	$I_S = 25 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	35	-	ns
Q <sub>r</sub>	recovered charge	V <sub>DS</sub> = 15 V; T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	[1]	-	28	-	nC
t <sub>a</sub>	reverse recovery rise time			-	17.3	-	ns
t <sub>b</sub>	reverse recovery fall time			-	17.9	-	ns
S	softness factor			-	1.03	-	
		1	1		1		1

#### [1] includes capacitive recovery

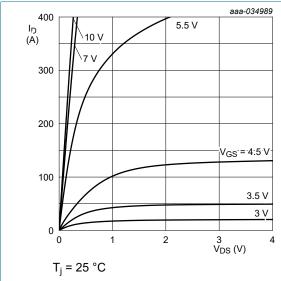


Fig. 7. Output characteristics; drain current as a function of drain-source voltage; typical values

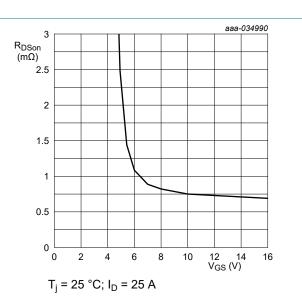


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

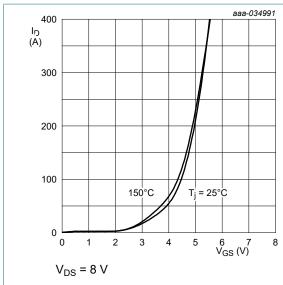


Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values

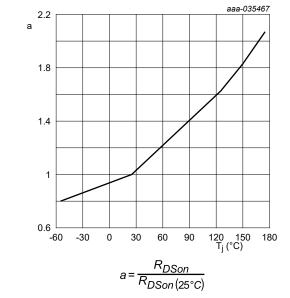


Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature

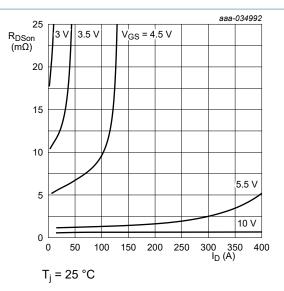


Fig. 10. Drain-source on-state resistance as a function of drain current; typical values

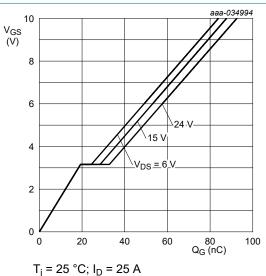


Fig. 12. Gate-source voltage as a function of gate charge; typical values

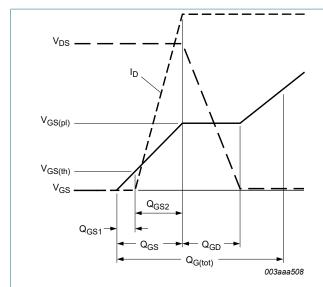


Fig. 13. Gate charge waveform definitions

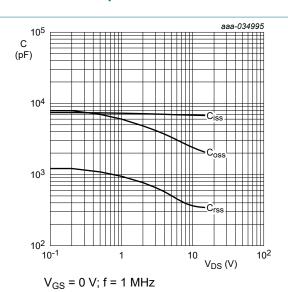


Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

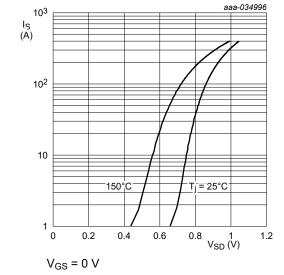


Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

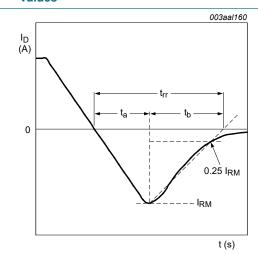
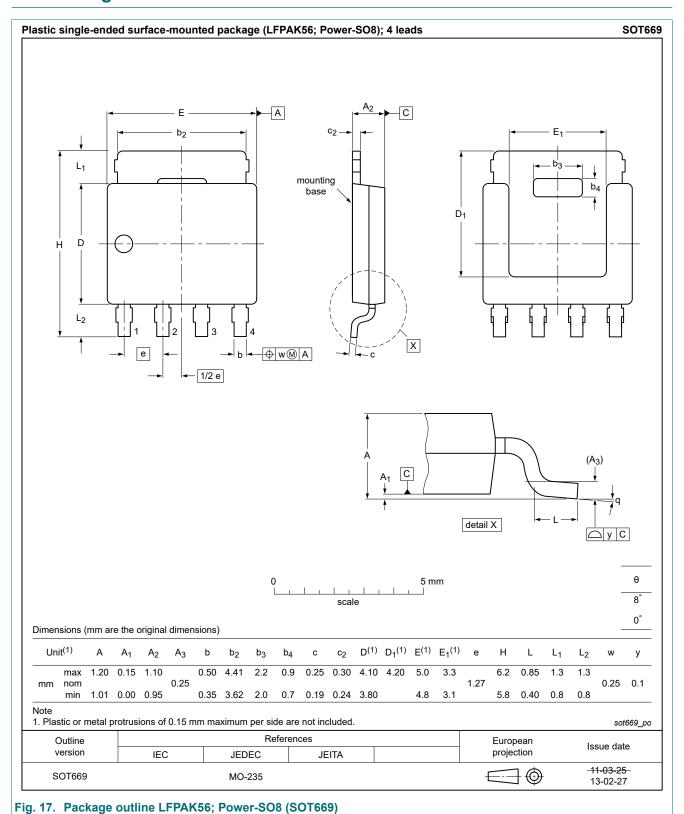
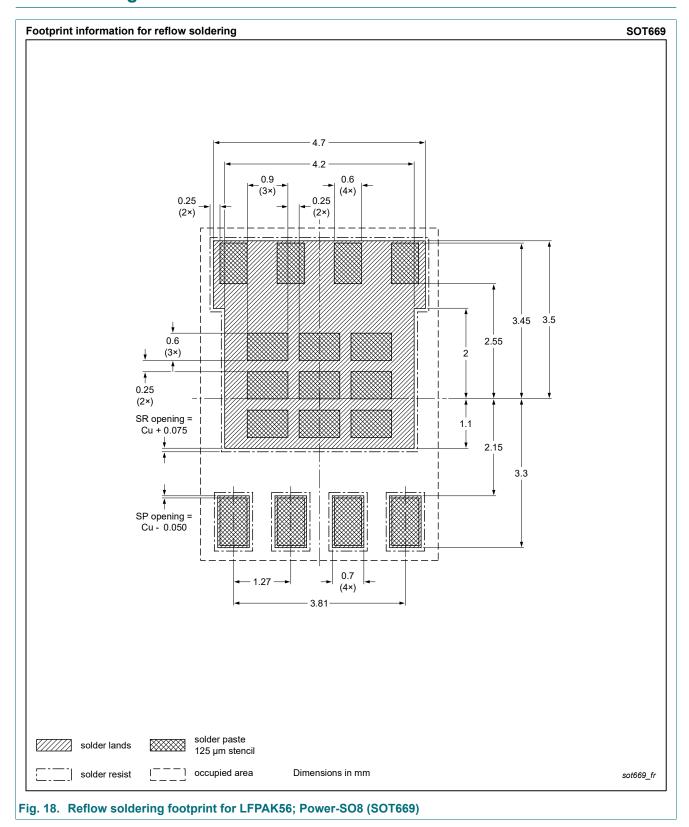


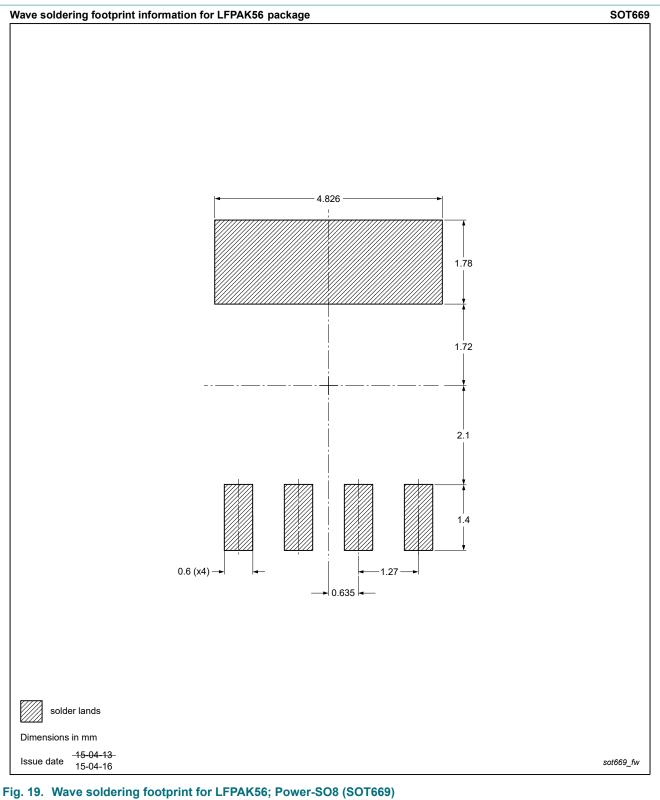
Fig. 16. Reverse recovery timing definition

## 11. Package outline



## 12. Soldering





### 13. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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